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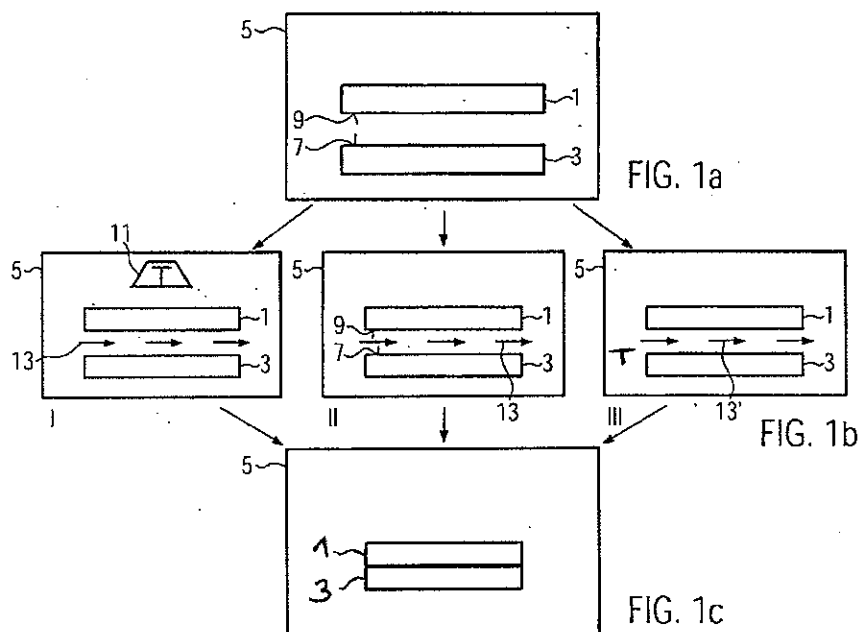
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(54) Title: PROCESSING FOR BONDING TWO SUBSTRATES



(57) Abstract: The invention relates to a method for bonding two substrates, in particular two semiconductor substrates which, in order to be able to improve the reliability of the process, provides the step of providing a gaseous flow over the bonding surfaces of the substrates. The invention also relates to a corresponding bonding equipment.

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